

# Switch-mode Power Rectifier 150 V, 20 A

## MBRF20H150CTG, MBR20H150CTG

### Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capability
- 20 A Total (10 A Per Diode Leg)
- Guard-Ring for Stress Protection
- These Devices are Pb-Free and are RoHS Compliant

### Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

### Mechanical Characteristics:

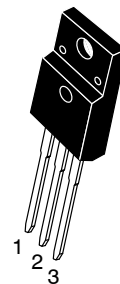
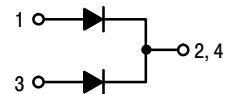
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams (TO-220 & TO-220FP)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



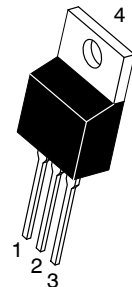
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## SCHOTTKY BARRIER RECTIFIER 20 AMPERES, 150 VOLTS



TO-220 FULLPAK™  
CASE 221D

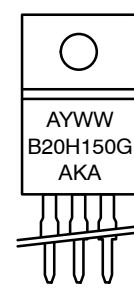


TO-220  
CASE 221A  
STYLE 6

### MARKING DIAGRAMS



TO-220



TO-220FP

A = Assembly Location  
Y = Year  
WW = Work Week  
B20H150 = Device Code  
G = Pb-Free Device  
AKA = Polarity Designator

### ORDERING INFORMATION

See detailed ordering and shipping information on page 1 of this data sheet.

# MBRF20H150CTG, MBR20H150CTG

## MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	150	V
Average Rectified Forward Current (Rated $V_R$ ) $T_C = 134^\circ\text{C}$	$I_{F(AV)}$	10 20	A (Per Leg) (Per Device)
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	$I_{FSM}$	180	A
Operating Junction Temperature (Note 1)	$T_J$	-20 to +150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-65 to +150	$^\circ\text{C}$
Voltage Rate of Change (Rated $V_R$ )	dv/dt	10,000	V/ $\mu\text{s}$
ESD Ratings:	Machine Model = C Human Body Model = 3B	> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

## THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum Thermal Resistance (MBR20H150CTG)	$R_{\theta JC}$	2.0	$^\circ\text{C}/\text{W}$
	- Junction-to-Case		
	$R_{\theta JA}$	45	
	- Junction-to-Ambient		
(MBRF20H150CTG)	$R_{\theta JC}$	2.5	
	- Junction-to-Case		

## ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Rating	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) ( $I_F = 5\text{ A}$ , $T_C = 25^\circ\text{C}$ ) ( $I_F = 5\text{ A}$ , $T_C = 125^\circ\text{C}$ ) ( $I_F = 10\text{ A}$ , $T_C = 25^\circ\text{C}$ ) ( $I_F = 10\text{ A}$ , $T_C = 125^\circ\text{C}$ )	$V_F$	0.72 0.57 0.87 0.65	0.60	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_C = 25^\circ\text{C}$ ) (Rated DC Voltage, $T_C = 125^\circ\text{C}$ )	$i_R$		50 30	$\mu\text{A}$ mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

## ORDERING INFORMATION

Device Order Number	Package Type	Shipping
MBRF20H150CTG	TO-220FP (Pb-Free)	50 Units / Rail
MBR20H150CTG	TO-220 (Pb-Free)	50 Units / Rail

# MBRF20H150CTG, MBR20H150CTG

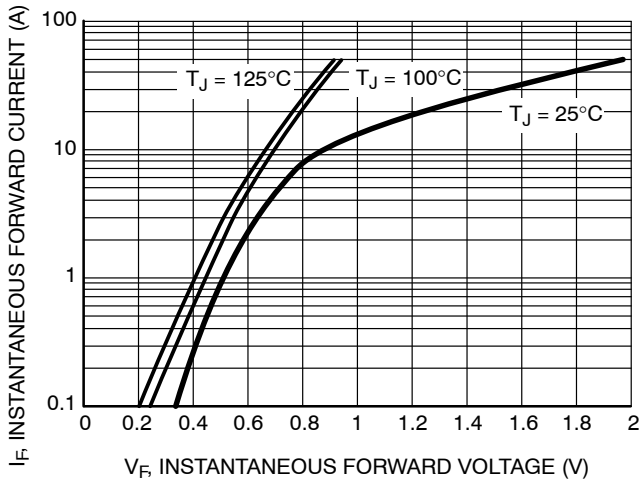


Figure 1. Typical Forward Voltage

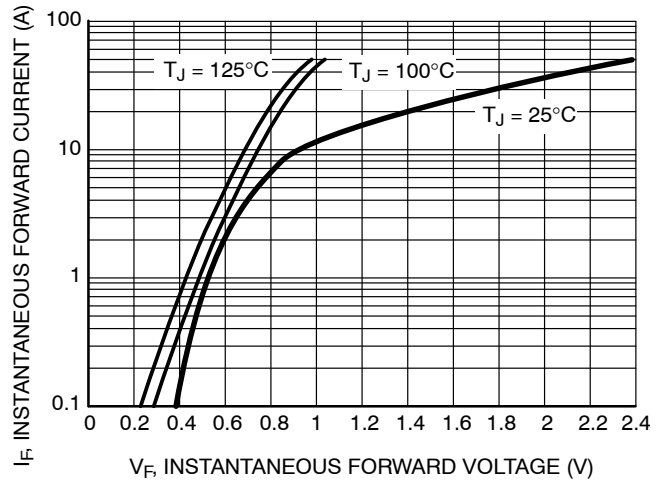


Figure 2. Maximum Forward Voltage

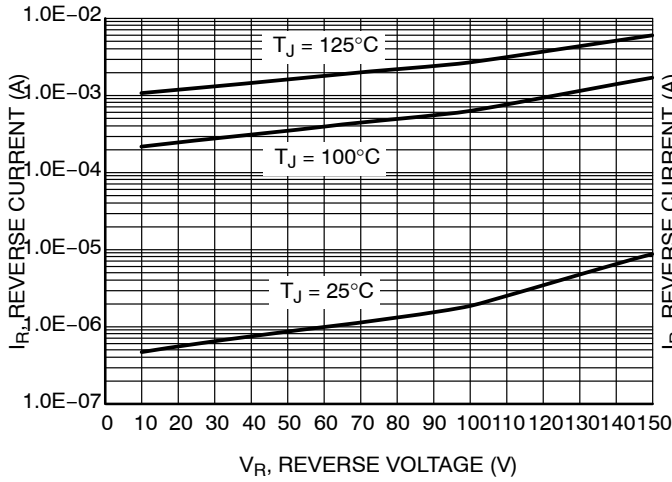


Figure 3. Typical Reverse Current

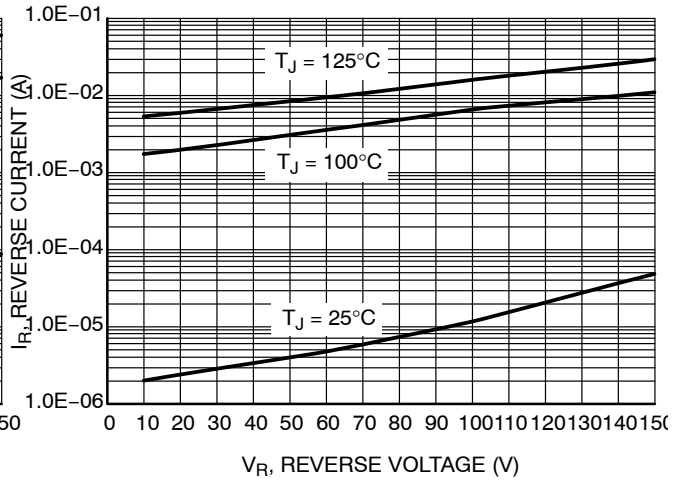


Figure 4. Maximum Reverse Current

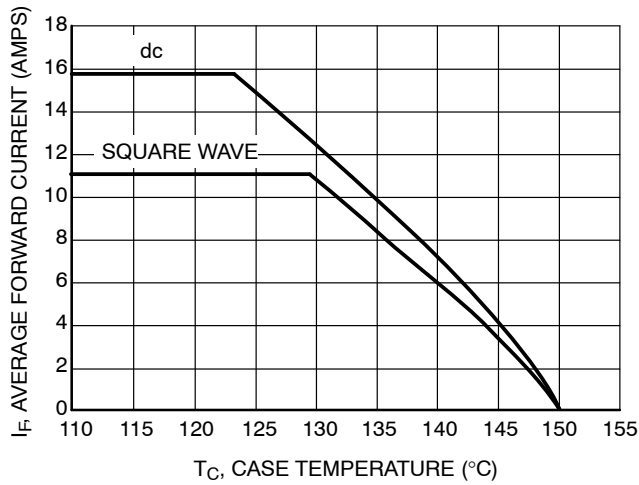


Figure 5. Current Derating

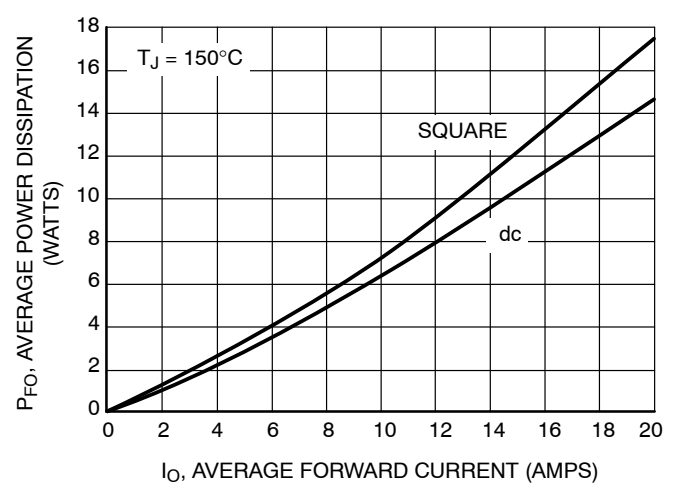


Figure 6. Forward Power Dissipation

# MBRF20H150CTG, MBR20H150CTG

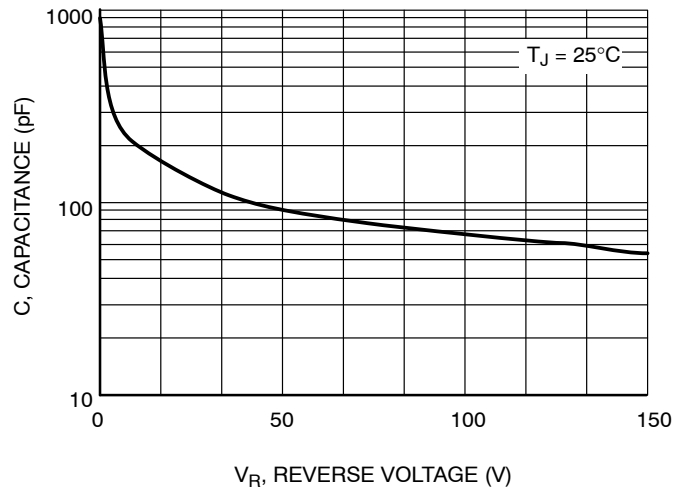


Figure 7. Capacitance

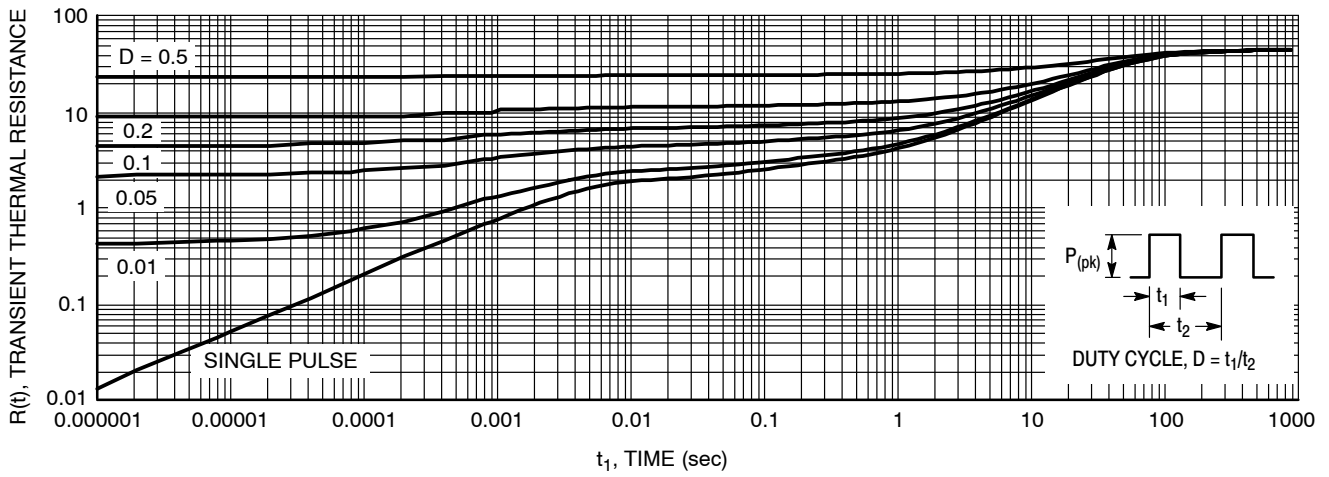


Figure 8. Thermal Response Junction-to-Ambient for MBR20H150CTG

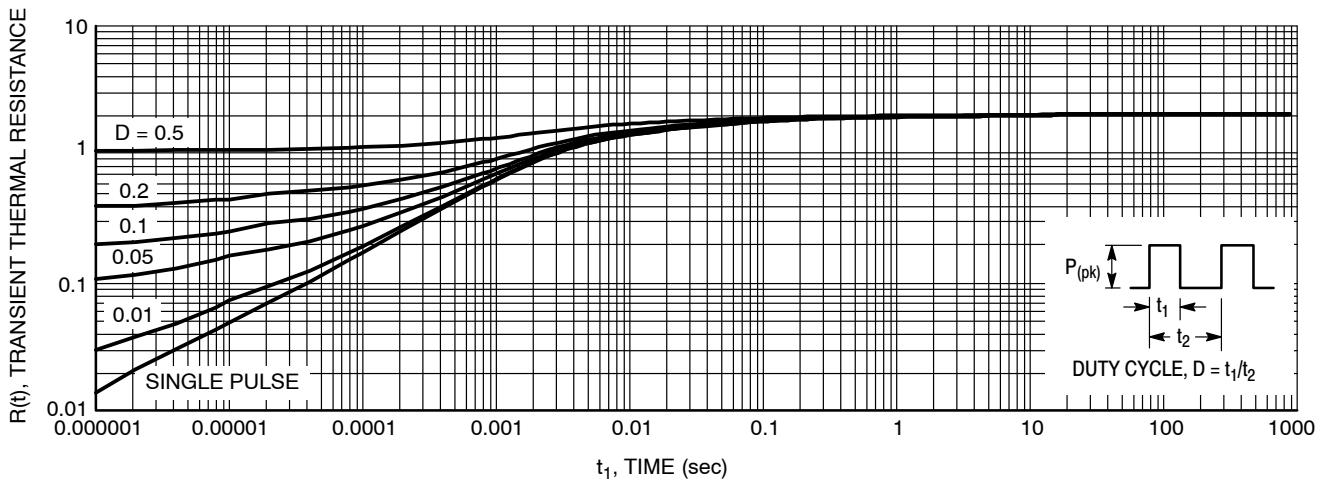


Figure 9. Thermal Response Junction-to-Case for MBR20H150CTG

# MBRF20H150CTG, MBR20H150CTG

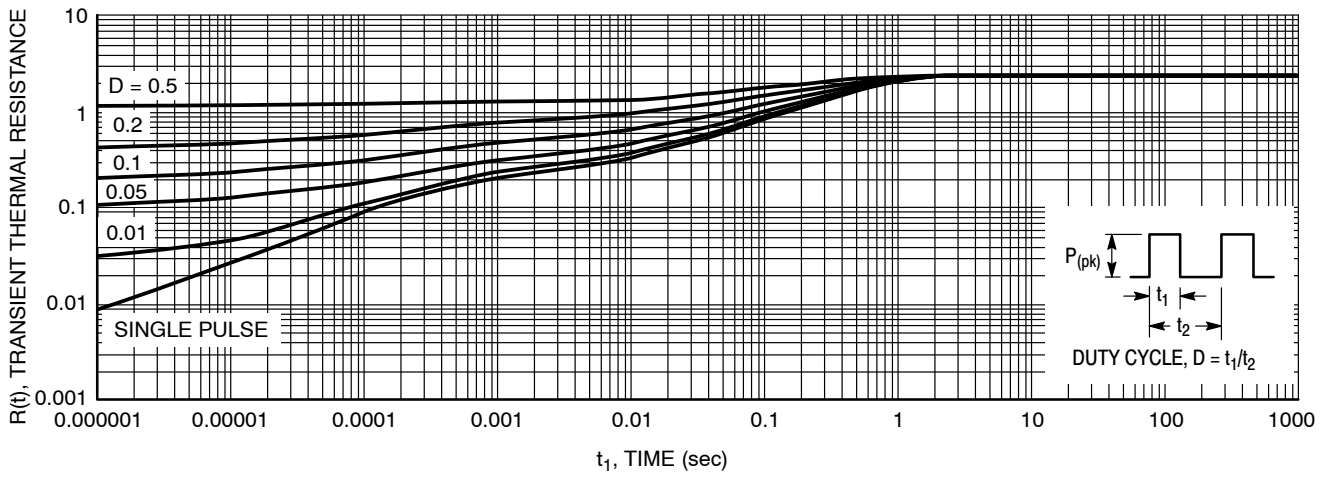


Figure 10. Thermal Response Junction-to-Case for MBRF20H150CTG

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



## TO-220 CASE 221A ISSUE AK

DATE 13 JAN 2022



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 2:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR  
4. EMITTER

STYLE 3:  
PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE

STYLE 4:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. MAIN TERMINAL 2

STYLE 5:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

STYLE 6:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

STYLE 7:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. ANODE

STYLE 8:  
PIN 1. CATHODE  
2. ANODE  
3. EXTERNAL TRIP/DELAY  
4. ANODE

STYLE 9:  
PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 10:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN  
4. SOURCE

STYLE 11:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE  
4. SOURCE

STYLE 12:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. NOT CONNECTED

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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

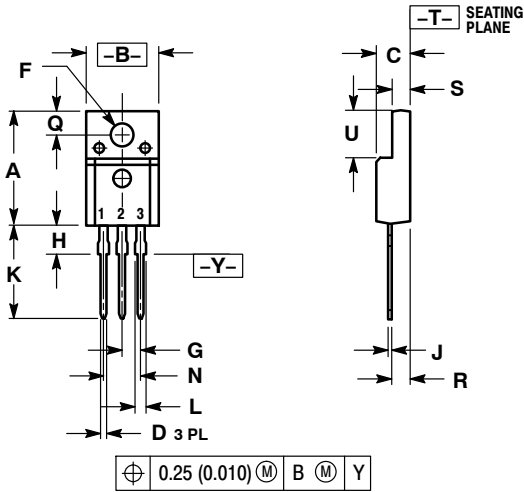
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SCALE 1:1

## TO-220 FULLPAK CASE 221D-03 ISSUE K

DATE 27 FEB 2009



- NOTES:
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  - CONTROLLING DIMENSION: INCH
  - 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

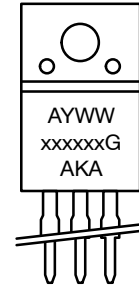
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.617	0.635	15.67	16.12
B	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
H	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

### MARKING DIAGRAMS

- |                                                      |                                                       |                                                    |
|------------------------------------------------------|-------------------------------------------------------|----------------------------------------------------|
| STYLE 1:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE     | STYLE 2:<br>PIN 1. BASE<br>2. COLLECTOR<br>3. EMITTER | STYLE 3:<br>PIN 1. ANODE<br>2. CATHODE<br>3. ANODE |
| STYLE 4:<br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE | STYLE 5:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE     | STYLE 6:<br>PIN 1. MT 1<br>2. MT 2<br>3. GATE      |



**Bipolar**



**Rectifier**

- |                               |                           |
|-------------------------------|---------------------------|
| xxxxxx = Specific Device Code | A = Assembly Location     |
| G = Pb-Free Package           | Y = Year                  |
| A = Assembly Location         | WW = Work Week            |
| Y = Year                      | xxxxxx = Device Code      |
| WW = Work Week                | G = Pb-Free Package       |
|                               | AKA = Polarity Designator |

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